

General Description

The QM2417C1 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the small power switching and load switch applications.

The QM2417C1 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-1	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-0.8	A
I_{DM}	Pulsed Drain Current ²	-5	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ³	0.33	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	375	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	240	°C/W

Product Summary


BVDSS

-20V

RDS(on)

240mΩ

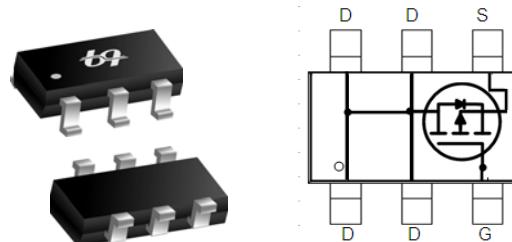
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Applications

- High Frequency Point-of-Load Synchronous s Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT363 (SC-70-6L) Pin Configuration



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

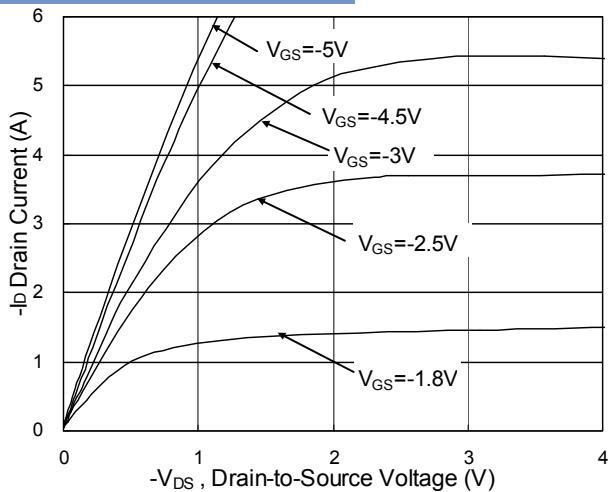
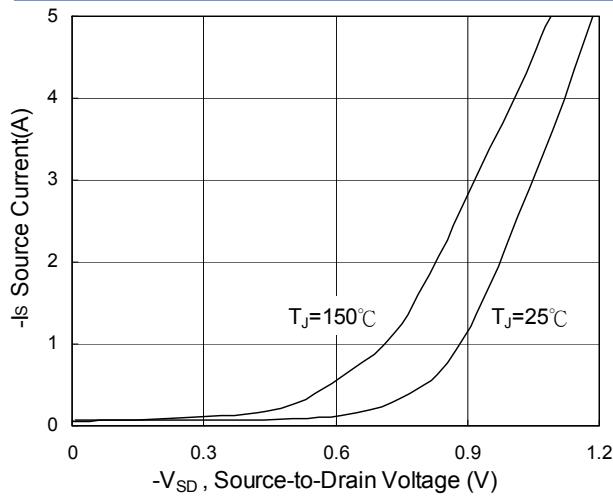
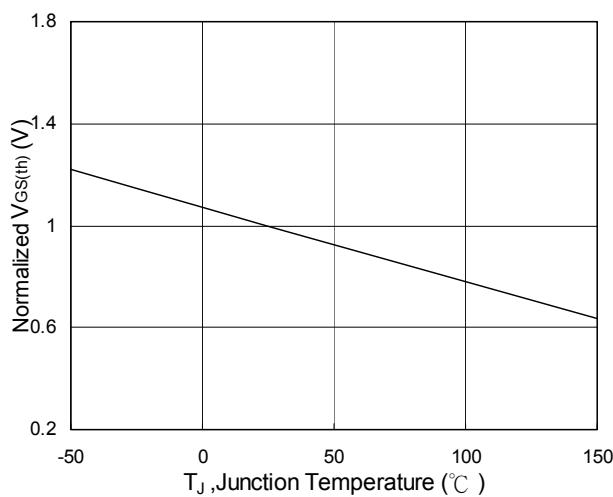
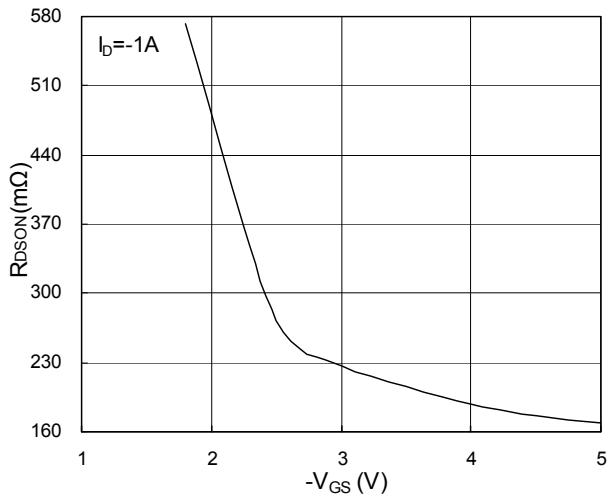
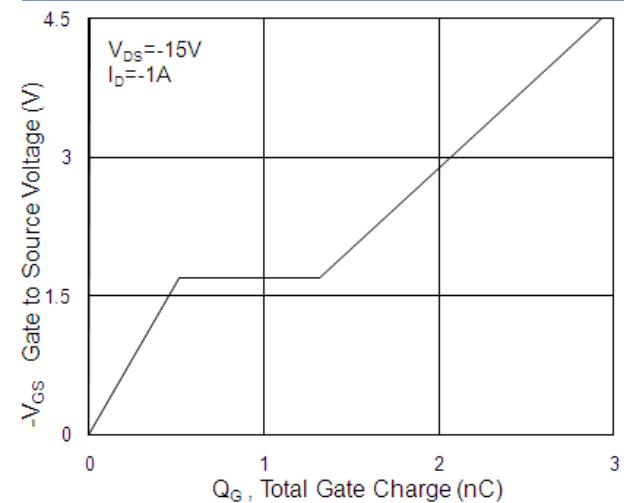
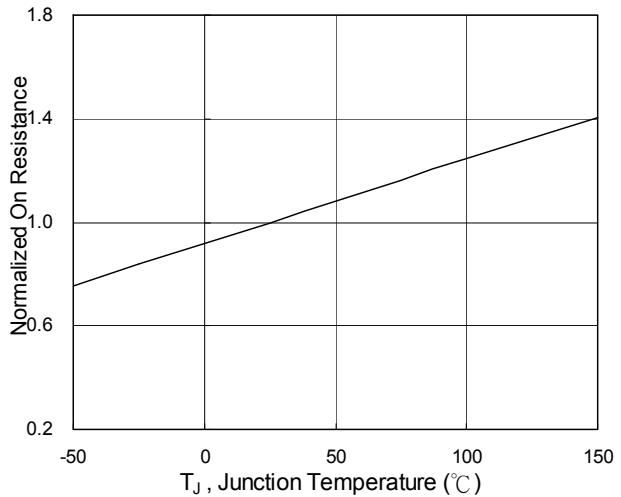
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.012	---	$\text{V}/^\circ\text{C}$
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{GS}=-4.5\text{V}$, $I_D=-1\text{A}$	---	185	240	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$, $I_D=-0.5\text{A}$	---	270	350	
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu\text{A}$	-0.5	-0.8	-1.2	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	2.2	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	-1	uA
		$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12\text{V}$, $V_{DS}=0\text{V}$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-1\text{A}$	---	3.1	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15\text{V}$, $V_{GS}=-4.5\text{V}$, $I_D=-1\text{A}$	---	2.9	4.1	nC
Q_{gs}	Gate-Source Charge		---	0.51	0.7	
Q_{gd}	Gate-Drain Charge		---	0.81	1.1	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-10\text{V}$, $V_{GS}=-4.5\text{V}$, $R_G=3.3\Omega$	---	2	4.0	ns
T_r	Rise Time		---	8	14.4	
$T_{d(off)}$	Turn-Off Delay Time		---	23	46	
T_f	Fall Time		---	14.8	29.6	
C_{iss}	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	---	190	266	pF
C_{oss}	Output Capacitance		---	33	46.2	
C_{rss}	Reverse Transfer Capacitance		---	27	37.8	

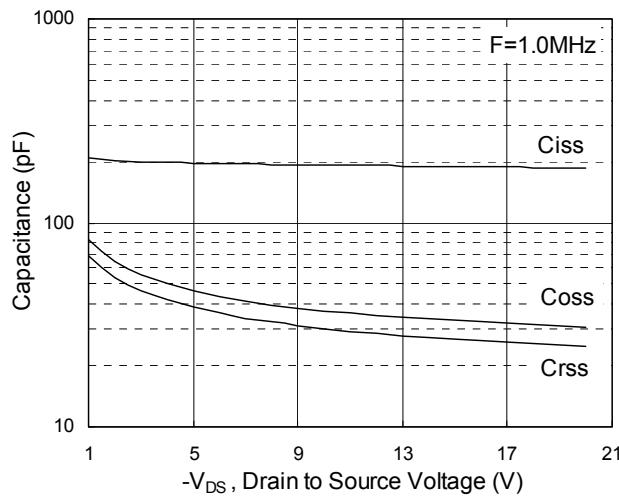
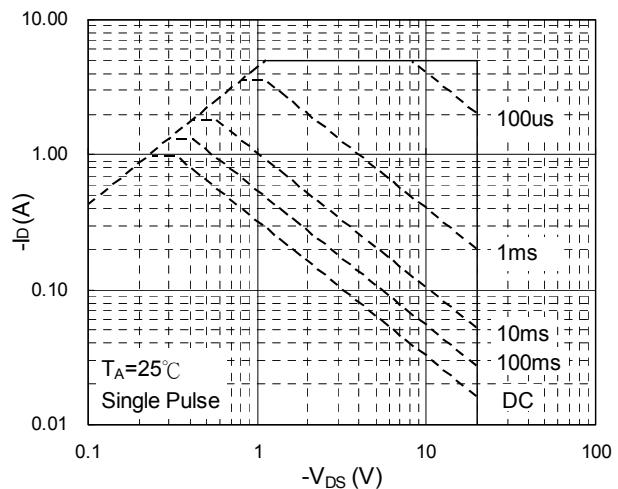
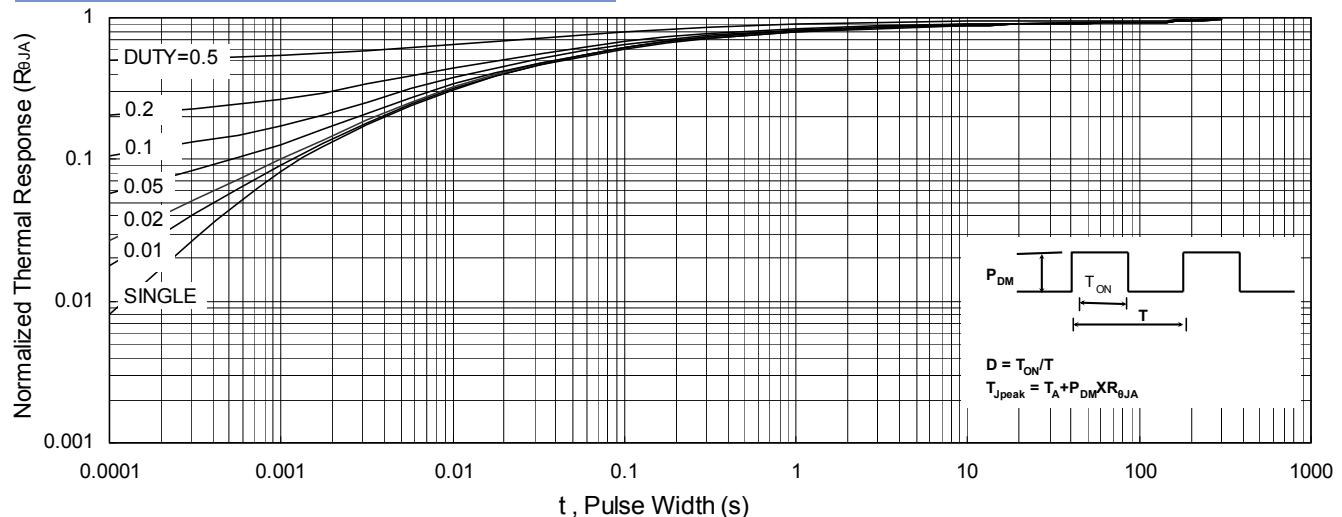
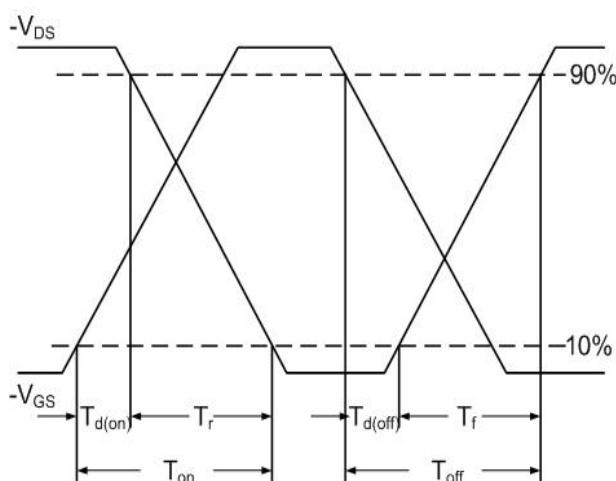
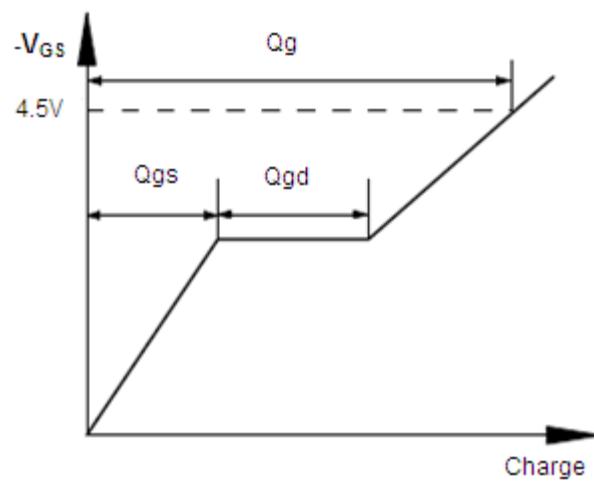
Drain-Source Body Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source-Drain Diode Current ^{1,4}	$V_G=V_D=0\text{V}$, Force Current	---	---	-1	A
I_{SM}	Pulsed Diode Forward Current ^{2,4}		---	---	-5	A
V_{SD}	Body Diode Voltage ²	$V_{GS}=0\text{V}$, $I_S=-1\text{A}$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-2\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$, $T_J=25^\circ\text{C}$	---	6.2	---	nS
Q_{rr}	Reverse Recovery Charge		---	2	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

Fig.1 Typical Output Characteristics

Fig.3 Forward Characteristics Of Reverse

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.2 On-Resistance vs. Gate-Source

Fig.4 Gate-Charge Characteristics

Fig.6 Normalized R_{DSON} vs. T_J

P-Ch 20V Fast Switching MOSFETs

Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform